

(Supplementary Information)

Space Charge-Induced Unusually-High Mobility of Solution-Processed Indium Oxide Thin Film Transistor with Ethylene Glycol Incorporated Aluminum Oxide Gate Dielectric

Hyungjin Park^{‡a}, Yunyong Nam^{‡a}, Jungho Jin^b, and Byeong-Soo Bae^{a}.*

^aLaboratory of Optical Materials and Coating (LOMC), Department of Materials Science and Engineering, Korea Advanced Institute of Science and Technology (KAIST), 291 Daehak-ro, Yuseong-gu, Daejeon 305-701, Korea.

^bMultiscale Hybrid Materials Laboratory (MHML), School of Materials Science and Engineering, University of Ulsan, 93 Daehak-ro, Nam-gu, Ulsan 680-749, Korea

*Corresponding author. E-mail address: bsbae@kaist.ac.kr

[‡]Both Hyungjin Park and YunYong Nam contributed equally.

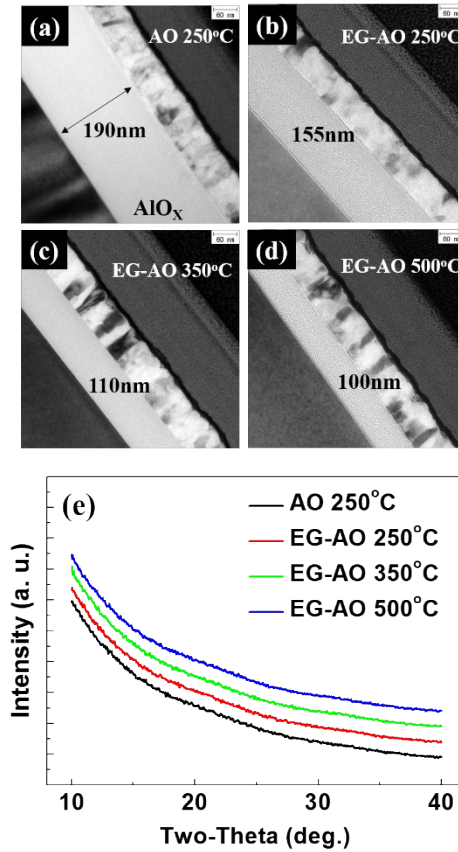


Fig. S1. Cross sectional TEM images of the gate dielectric layer: (a) AO 250oC, (b) EG-AO 250oC, (c) EG-AO 350oC, and (d) EG-AO 500oC. (e) XRD spectra of AO and EG-AO gate dielectric layers annealed at various temperatures.

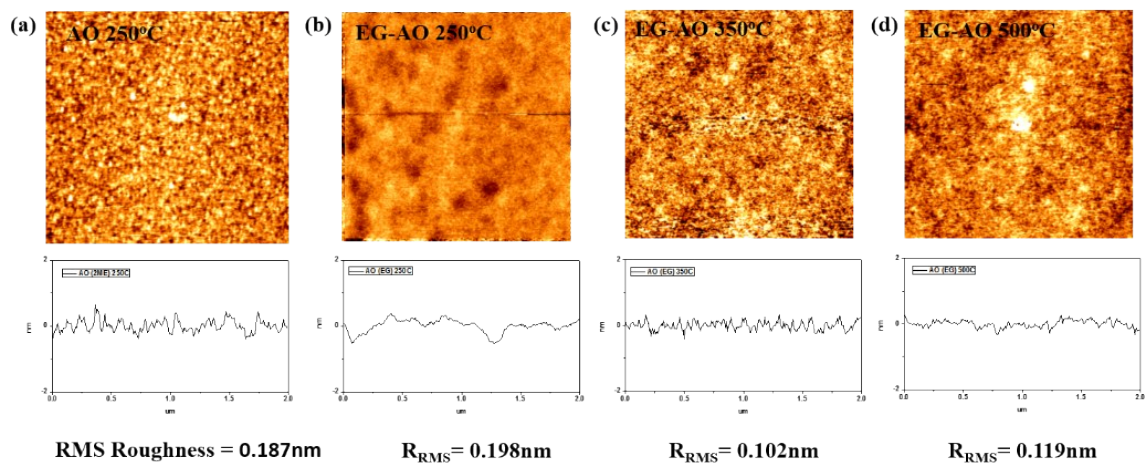


Fig. S2. AFM images and line profiles of (a) AO 250°C, (b) EG-AO 250°C, (c) EG-AO 350°C, and EG-AO 500°C gate dielectric layer.

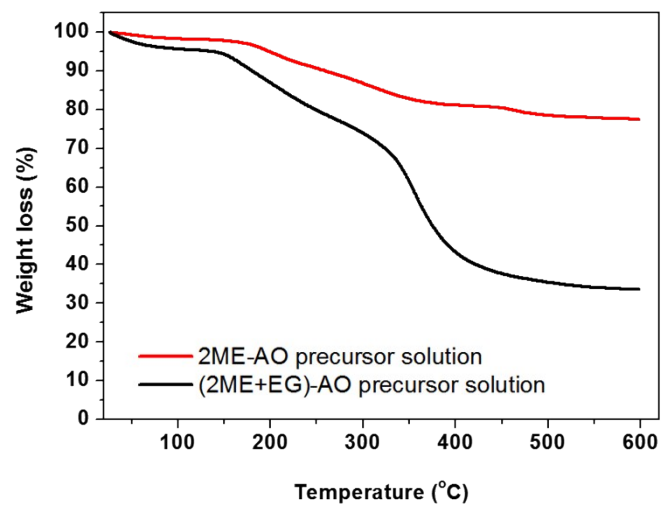


Fig. S3. TGA results of AO precursor solution (only 2-ME for solvent) and EG-AO precursor solution (both 2-ME and EG) after drying 120 °C.